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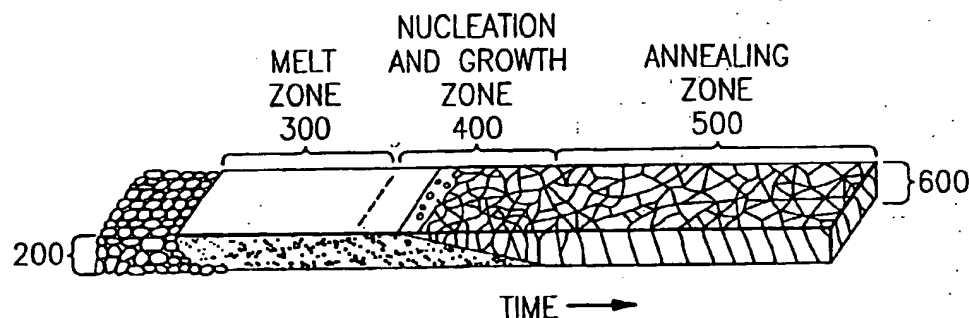
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(54) Title: SEMICONDUCTOR ELEMENTS HAVING ZONES OF REDUCED OXYGEN



(57) Abstract: There is provided a structure comprising semiconductor material (600), the structure having at least one zone of reduced oxygen concentration, such zone having an interstitial oxygen concentration of not greater than 3×10^{17} oxygen atoms/cm³, such zone extending at least 75 microns in depth from a first major surface. There is further provided a photovoltaic cell comprising at least one such structure.

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